IOR HiRel
An Infineon Technologies Company

IRHLUC7670Z4
2N7632UC

RADIATION HARDENED LOGIC LEVEL POWER MOSFET SURFACE MOUNT (LCC-6)

60V, COMBINATION 1N-1P CHANNEL R7 TECHNOLOGY

LCC-6

Product Summary

Part Number	Radiation Level	$R_{DS(on)}$	I_D	Channel
IRHLUC7670Z4	100 kRads(Si)	0.75Ω	0.89A	N
IRHLUC7630Z4	300 kRads(Si)	0.75Ω	0.89A	N
IRHLUC7670Z4	100 kRads(Si)	1.6Ω	-0.65A	P
IRHLUC7630Z4	300 kRads(Si)	1.6Ω	-0.65A	P

Description

IR HiRel R7 Logic Level Power MOSFETs provide simple solution to interfacing CMOS and TTL control circuits to power devices in space and other radiation environments. The threshold voltage remains within acceptable operating limits over the full operating temperature and post radiation. This is achieved while maintaining single event gate rupture and single event burnout immunity.

The device is ideal when used to interface directly with most logic gates, linear IC's, micro-controllers, and other device types that operate from a 3.3-5V source. It may also be used to increase the output current of a PWM, voltage comparator or an operational amplifier where the logic level drive signal is available.

Features

- 5V CMOS and TTL Compatible
- Low Rds(on)
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Light Weight
- Hermetically Sealed
- Surface Mount
- ESD Rating: Class 0 per MIL-STD-750, Method 1020

Absolute Maximum Ratings (N-Ch Die and P-Ch Die) — Pre-Irradiation

Symbol	Parameter	N-Channel	P-Channel	Units
I_{D1} @ V_{GS} = ±4.5V, T_C = 25°C	Continuous Drain Current	0.89	-0.65	A
I_{D2} @ V_{GS} = ±4.5V, T_C = 100°C	Continuous Drain Current	0.56	-0.41	
I_{DM}	Pulsed Drain Current ①	3.56	-2.6	
P_D @T_C = 25°C	Maximum Power Dissipation	1.0	1.0	W
	Linear Derating Factor	0.01	0.01	W/°C
V_{GS}	Gate-to-Source Voltage	± 10	± 10	V
E_{AS}	Single Pulse Avalanche Energy ②	20	34	mJ
I_{AR}	Avalanche Current ①	0.89	-0.65	A
E_{AR}	Repetitive Avalanche Energy ①	0.1	0.1	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.7	-5.6	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150		°C
	Package Mounting Surface Temperature	300 (for 5s)		
	Weight	0.2 (Typical)		g

For Footnotes, refer to the page 2 for N Channel and page 3 for P Channel

Electrical Characteristics (N-Ch Die) @ Tj = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.07	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.75	Ω	V_{GS} = 4.5V, I_{D2} = 0.56A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-4.5	—	mV/°C	
Gfs	Forward Transconductance	1.1	—	—	S	V_{DS} = 15V, I_{D2} = 0.56A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	1.0	µA	V_{DS} = 48V, V_{GS} = 0V
		—	—	10		V_{DS} = 48V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 10V
	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -10V
Q_G	Total Gate Charge	—	—	3.6	nC	I_{D1} = 0.89A
Q_{GS}	Gate-to-Source Charge	—	—	1.5		V_{DS} = 30V
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	1.8		V_{GS} = 4.5V
$t_{d(on)}$	Turn-On Delay Time	—	—	8.0	ns	V_{DD} = 30V
tr	Rise Time	—	—	15		I_{D1} = 0.89A
$t_{d(off)}$	Turn-Off Delay Time	—	—	30		R_G = 24Ω
t_f	Fall Time	—	—	12		V_{GS} = 5.0V
Ls +L_D	Total Inductance	—	33	—	nH	Measured from center of Drain pad to center of Source pad
C_{iss}	Input Capacitance	—	145	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	43	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	2.5	—		f = 1.0MHz
R_G	Gate Resistance	—	9.5	—	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics (N-Ch Die)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	0.89	A	
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	3.56		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	T_J=25°C,I_S = 0.89A, V_{GS}= 0V④
t_{rr}	Reverse Recovery Time	—	—	65	ns	T_J=25°C, I_F = 0.89A, V_{DD} ≤ 25V
Q_{rr}	Reverse Recovery Charge	—	—	67	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Thermal Resistance (N-Ch Die)

Symbol	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient	—	—	125	°C/W
$R_{\theta JL}$	Junction-to-Lead	—	—	40	

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = 25V, starting T_J = 25°C, L = 50.4mH, Peak I_L = 0.89A, V_{GS} = 10V

③ I_{SD} ≤ .0.89A, di/dt ≤ 200A/µs, V_{DD} ≤ 60V, T_J ≤ 150°C

④ Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

⑤ Total Dose Irradiation with V_{GS} Bias. 10 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

⑥ Total Dose Irradiation with V_{DS} Bias. 48 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Electrical Characteristics (P-Ch Die) @ Tj = 25°C (Unless Otherwise Specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	V_{GS} = 0V, I_D = -250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.06	—	V/°C	Reference to 25°C, I_D = -1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	1.6	Ω	V_{GS} = -4.5V, I_{D2} = -0.41A ④
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-2.0	V	V_{DS} = V_{GS}, I_D = -250µA
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	3.6	—	mV/°C	
Gfs	Forward Transconductance	0.6	—	—	S	V_{DS} = -15V, I_{D2} = -0.41A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	-1.0	µA	V_{DS} = -48V, V_{GS} = 0V
		—	—	-20		V_{DS} = -48V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V_{GS} = -10V
	Gate-to-Source Leakage Reverse	—	—	100		V_{GS} = 10V
Q_G	Total Gate Charge	—	—	3.6	nC	I_{D1} = -0.65A
Q_{GS}	Gate-to-Source Charge	—	—	1.5		V_{DS} = -30V
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	1.8		V_{GS} = -4.5V
$t_{d(on)}$	Turn-On Delay Time	—	—	23	ns	V_{DD} = -30V
tr	Rise Time	—	—	22		I_{D1} = -0.65A
$t_{d(off)}$	Turn-Off Delay Time	—	—	32		R_G = 24Ω
t_f	Fall Time	—	—	26		V_{GS} = 5.0V
Ls +L_D	Total Inductance	—	33	—	nH	Measured from center of Drain pad to center of Source pad
C_{iss}	Input Capacitance	—	147	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	46	—		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	—	8.1	—		f = 1.0MHz
R_G	Gate Resistance	—	52	—	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics (P-Ch Die)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-0.65	A	
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-2.6		
V_{SD}	Diode Forward Voltage	—	—	-5.0	V	T_J=25°C,I_S =-0.65A, V_{GS}= 0V④
t_{rr}	Reverse Recovery Time	—	—	35	ns	T_J=25°C,I_F=-0.65A,V_{DD} ≤ –25V
Q_{rr}	Reverse Recovery Charge	—	—	9.8	nC	di/dt = -100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Thermal Resistance (P-Ch Die)

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient	—	—	125	°C/W
$R_{\theta JL}$	Junction-to-Lead	—	—	40	

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = -25V, starting T_J = 25°C, L = 161mH, Peak I_L = -0.65A, V_{GS} = -10V

③ I_{SD} ≤ .-0.65A, di/dt ≤ -150A/µs, V_{DD} ≤ -60V, T_J ≤ 150°C

④ Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

⑤ Total Dose Irradiation with V_{GS} Bias. -10 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

⑥ Total Dose Irradiation with V_{DS} Bias. -48 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Radiation Characteristics

IR HiRel Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-39 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics (N-Ch Die) @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

Symbol	Parameter	Up to 300 kRads (Si) [1]		Units	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	——	V	V_{GS} = 0V, I_D = 250µA
$V_{GS(th)}$	Gate Threshold Voltage	1.0	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{GSS}	Gate-to-Source Leakage Forward	——	100	nA	V_{GS} = 10V
I_{GSS}	Gate-to-Source Leakage Reverse	——	-100	nA	V_{GS} = -10V
I_{DSS}	Zero Gate Voltage Drain Current	——	1.0	µA	V_{DS} = 48V, V_{GS} = 0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-39)	——	0.65	Ω	V_{GS} = 4.5V, I_{D2} = 0.56A
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (LCC-6)	——	0.75	Ω	V_{GS} = 4.5V, I_{D2} = 0.56A
V_{SD}	Diode Forward Voltage	——	1.2	V	V_{GS} = 0V, I_S = 0.89A

1. Part numbers IRHLUC7670Z4 and IRHLUC7630Z4

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area (N-Ch Die)

LET (MeV/(mg/cm²))	Energy (MeV)	Range (µm)	VDS (V)					
			@ VGS = 0V	@ VGS = -2V	@ VGS = -3V	@ VGS = -4V	@ VGS = -5V	@ VGS = -6V
38.1	358	43.9	60	60	60	60	60	60
60.9	659	54	60	60	60	60	60	——
90.7	1375	75.4	60	60	——	——	——	——

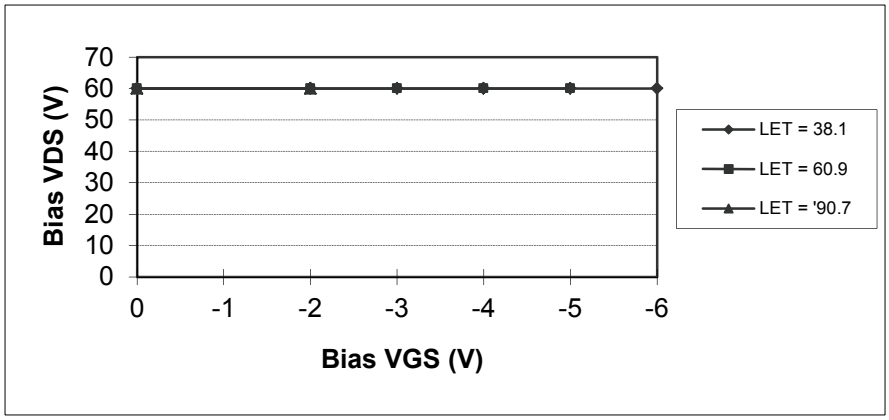


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 2.

Radiation Characteristics

IR HiRel Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-39 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics (P-Ch Die) @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	Up to 300 kRads (Si) [1]		Units	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	-60	——	V	V_{GS} = 0V, I_D = -250µA
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	-2.0	V	V_{DS} = V_{GS}, I_D = -250µA
I_{GSS}	Gate-to-Source Leakage Forward	——	-100	nA	V_{GS} = -10V
I_{GSS}	Gate-to-Source Leakage Reverse	——	100	nA	V_{GS} = 10V
I_{DSS}	Zero Gate Voltage Drain Current	——	-1.0	µA	V_{DS} = 48V, V_{GS} = 0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-39)	——	1.4	Ω	V_{GS} = -4.5V, I_{D2} = -0.41A
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (LCC-6)	——	1.6	Ω	V_{GS} = -4.5V, I_{D2} = -0.41A
V_{SD}	Diode Forward Voltage	——	-5.0	V	V_{GS} = 0V, I_S = -0.65A

1. Part numbers IRHLUC7670Z4 and IRHLUC7630Z4

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area (P-Ch Die)

LET (MeV/(mg/cm²))	Energy (MeV)	Range (µm)	VDS (V)					
			@ VGS =0V	@ VGS =2V	@ VGS =4V	@ VGS =5V	@ VGS =6V	@ VGS =7V
38 ± 5%	300 ± 7.5%	38 ± 7.5%	-60	-60	-60	-60	-60	-60
62 ± 5%	355 ± 7.5%	33 ± 7.5%	-60	-60	-60	-60	-60	——
85 ± 5%	380 ± 7.5%	29 ± 7.5%	-60	-60	-60	-60	——	——

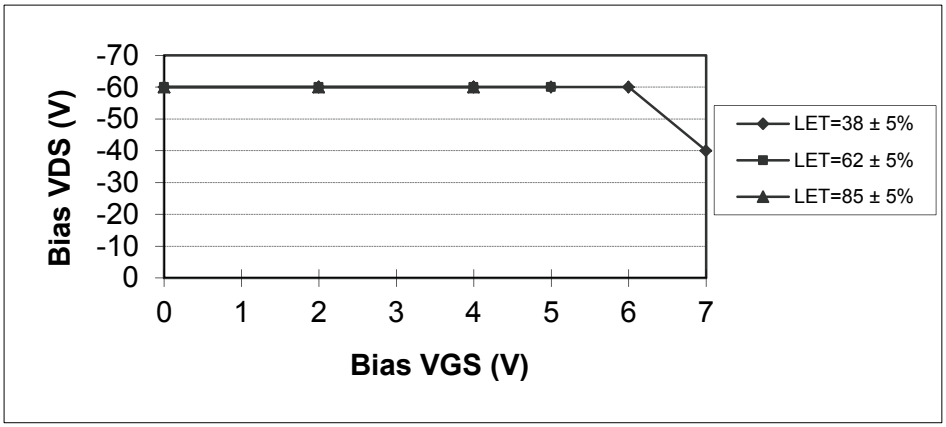


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 3.

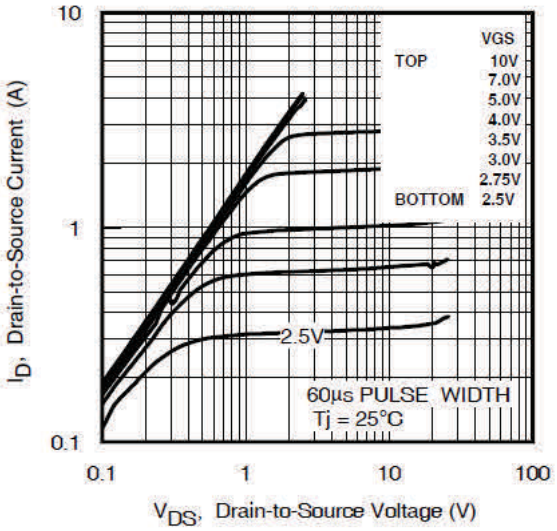


Fig 1. Typical Output Characteristics

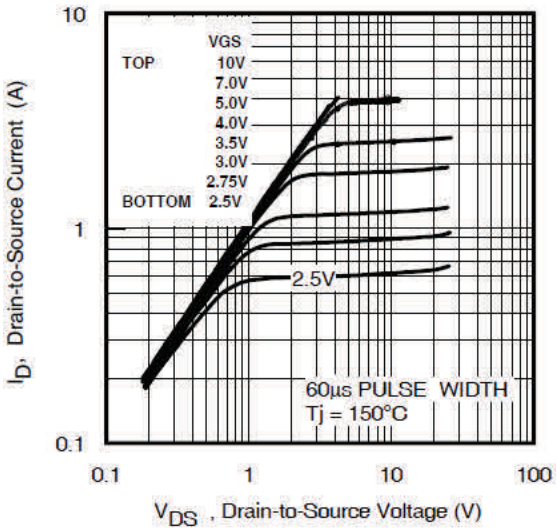


Fig 2. Typical Output Characteristics

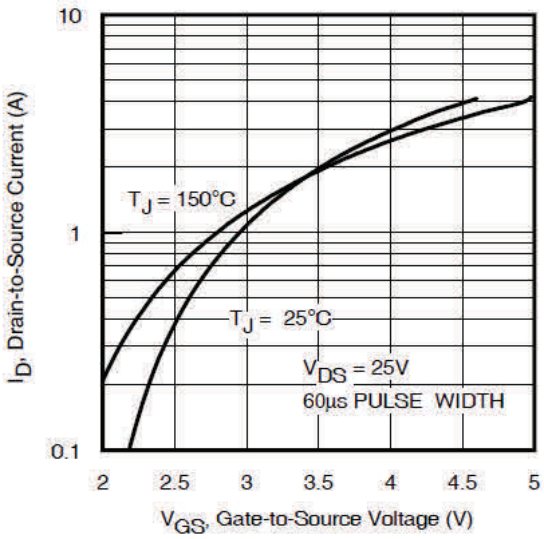


Fig 3. Typical Transfer Characteristics

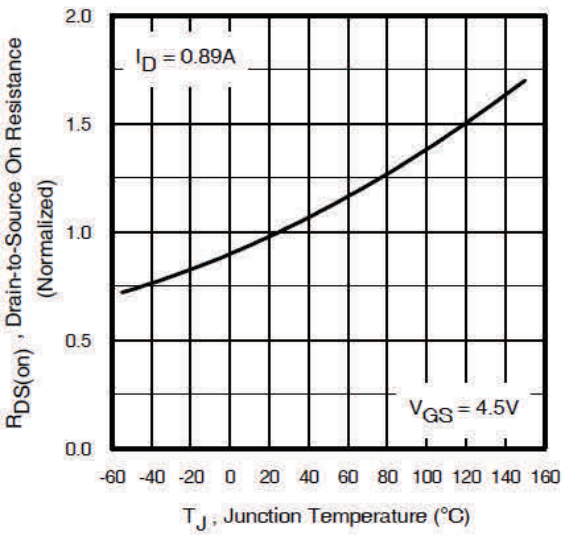


Fig 4. Normalized On-Resistance Vs. Temperature

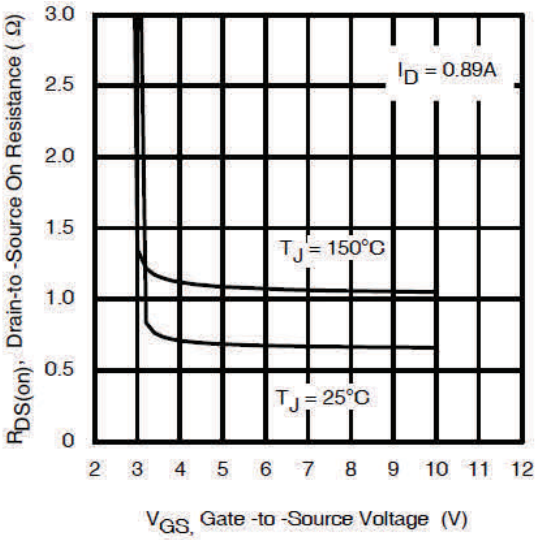


Fig 5. Typical On-Resistance Vs Gate Voltage

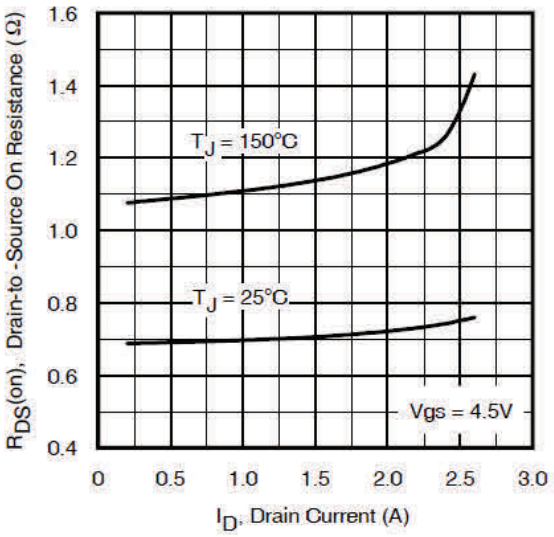


Fig 6. Typical On-Resistance Vs Drain Current

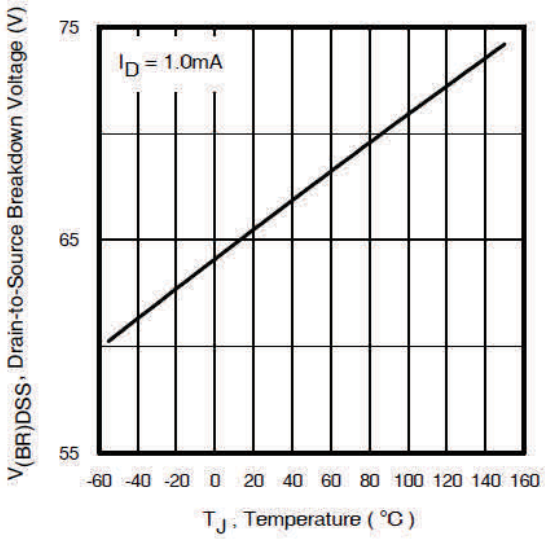


Fig 7. Typical Drain-to-Source Breakdown Voltage Vs Temperature

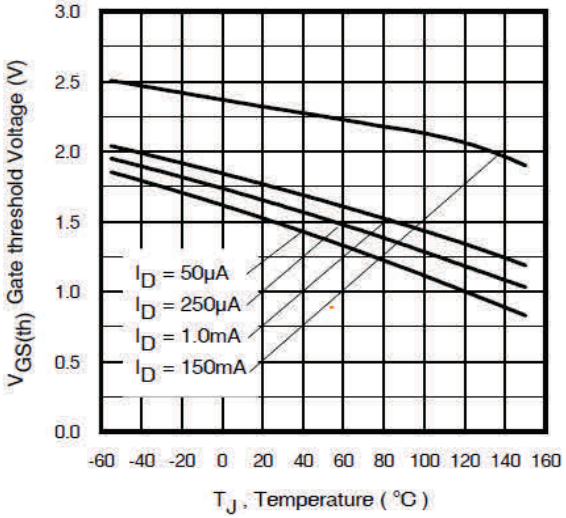


Fig 8. Typical Threshold Voltage Vs Temperature

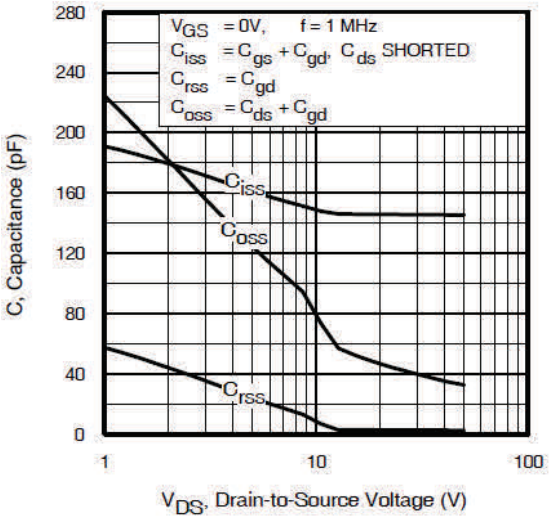


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

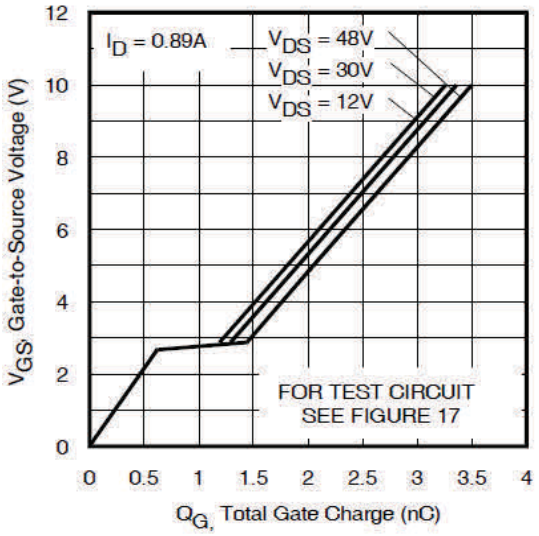


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

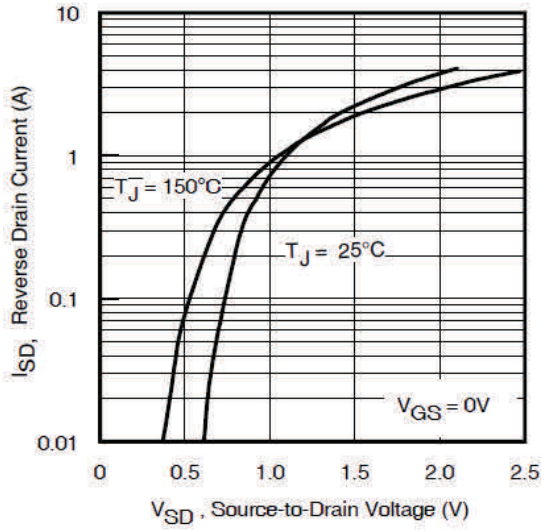


Fig 11. Typical Source-Drain Diode Forward Voltage

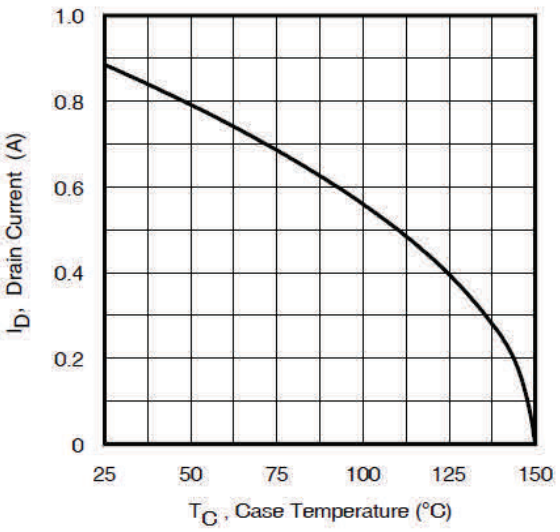


Fig 12. Maximum Drain Current Vs.Case Temperature

N-Channel
Die 1

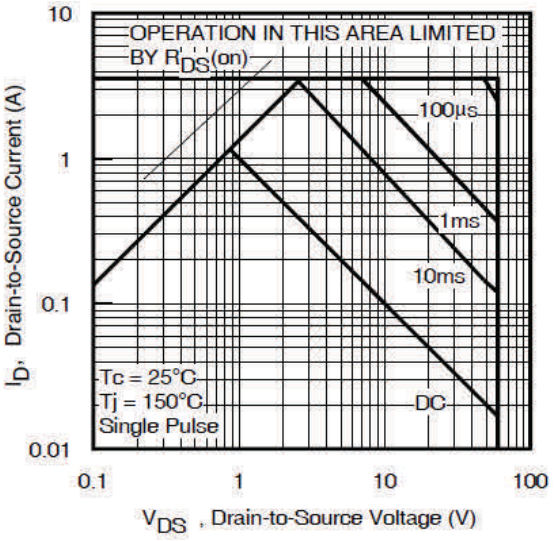


Fig 13. Maximum Safe Operating Area

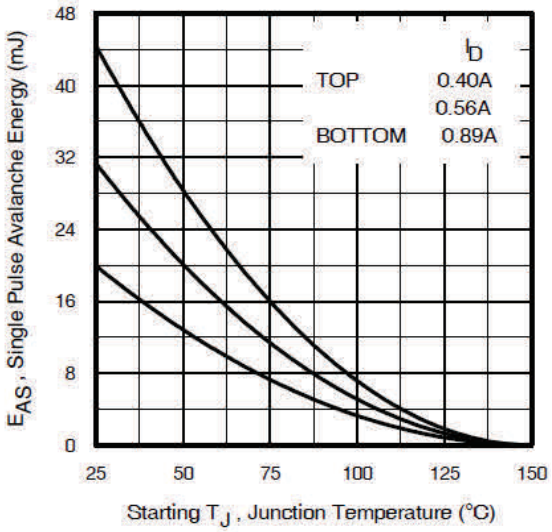


Fig 14. Maximum Avalanche Energy Vs. Drain Current

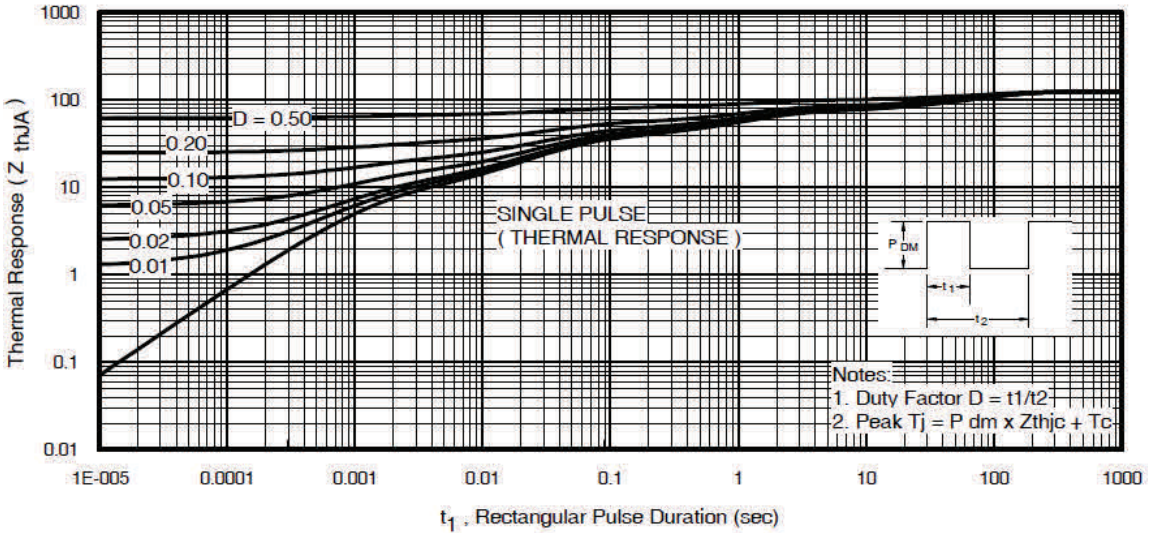


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

N-Channel
Die 1

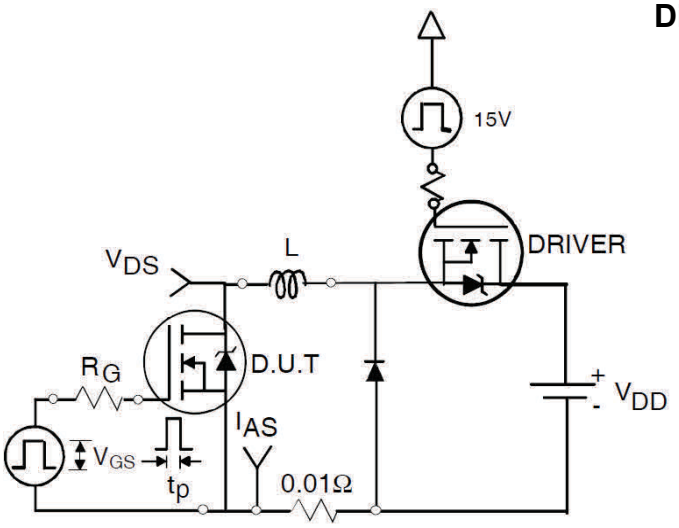


Fig 16a. Unclamped Inductive Test Circuit

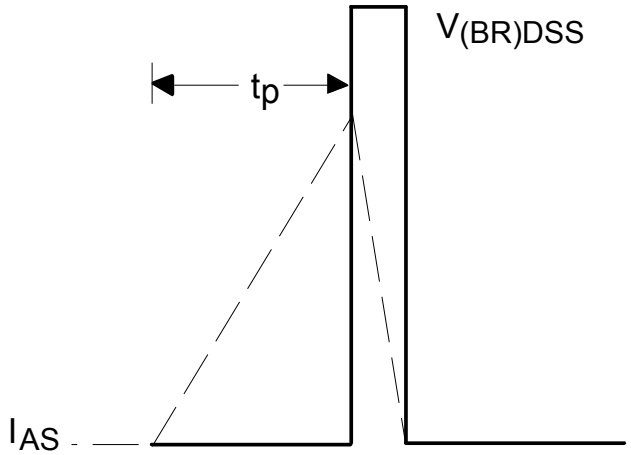


Fig 16b. Unclamped Inductive Waveforms

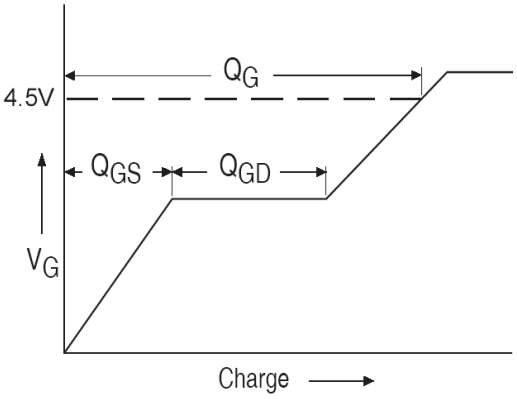


Fig 17a. Gate Charge Waveform

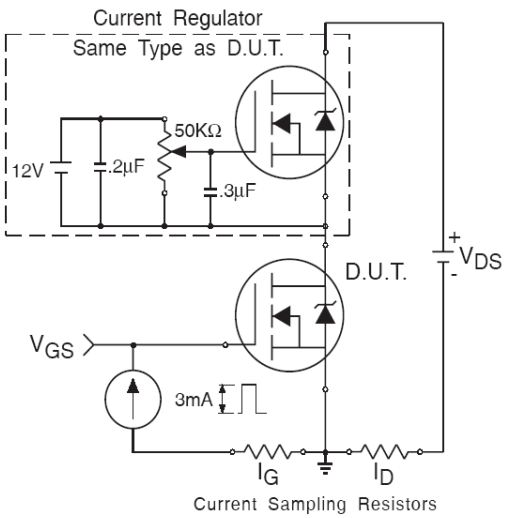


Fig 17b. Gate Charge Test Circuit

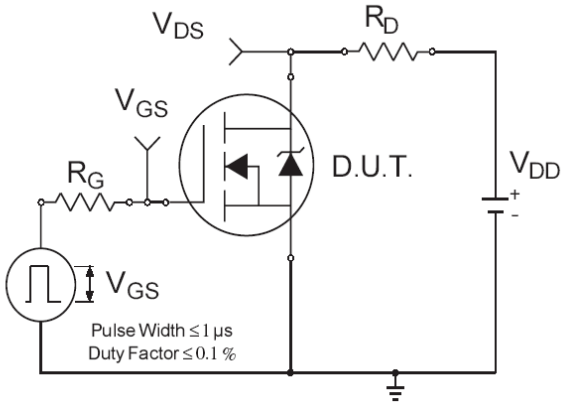


Fig 18a. Switching Time Test Circuit

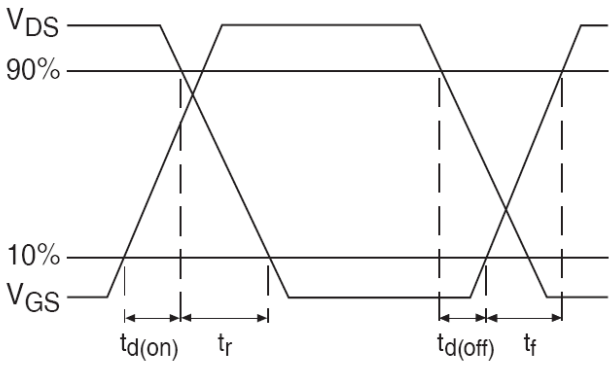


Fig 18b. Switching Time Waveforms

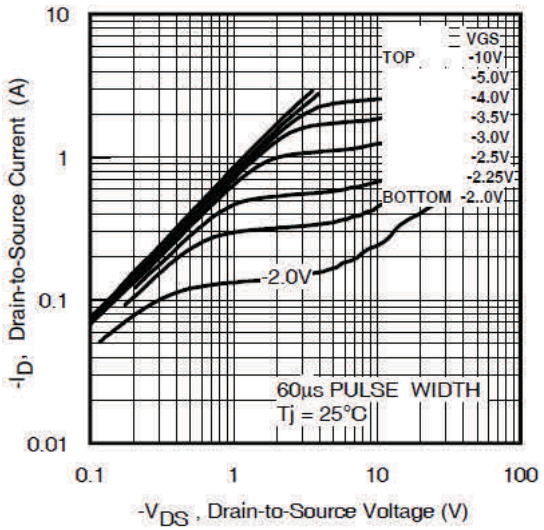


Fig 1. Typical Output Characteristics

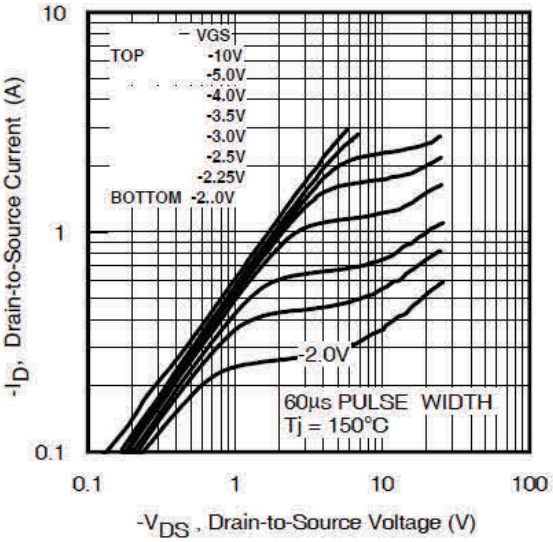


Fig 2. Typical Output Characteristics

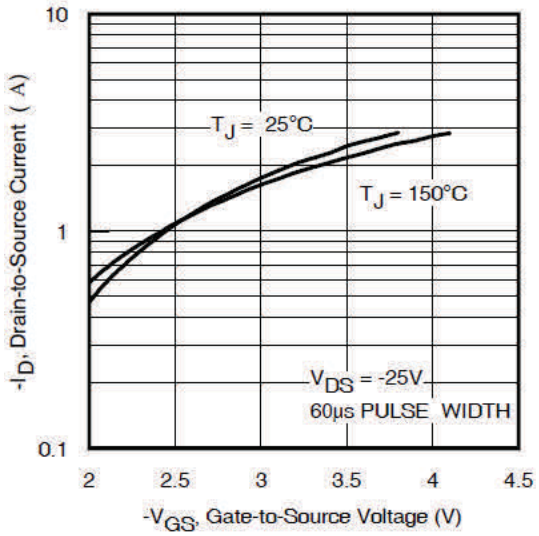


Fig 3. Typical Transfer Characteristics

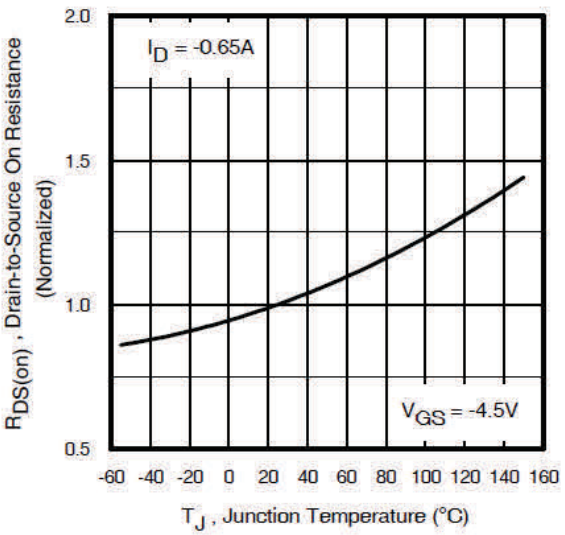


Fig 4. Normalized On-Resistance Vs. Temperature

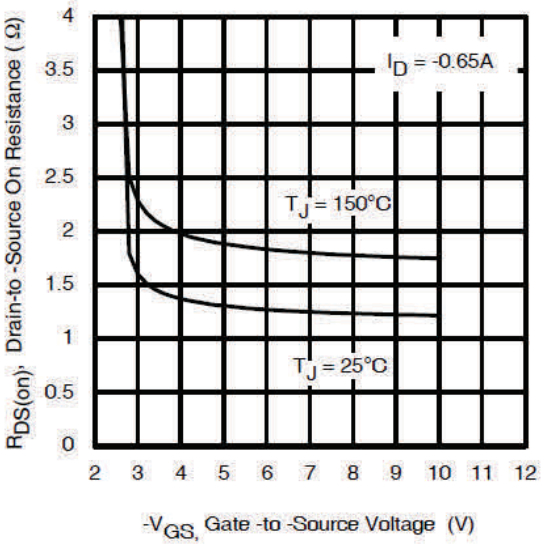


Fig 5. Typical On-Resistance Vs Gate Voltage

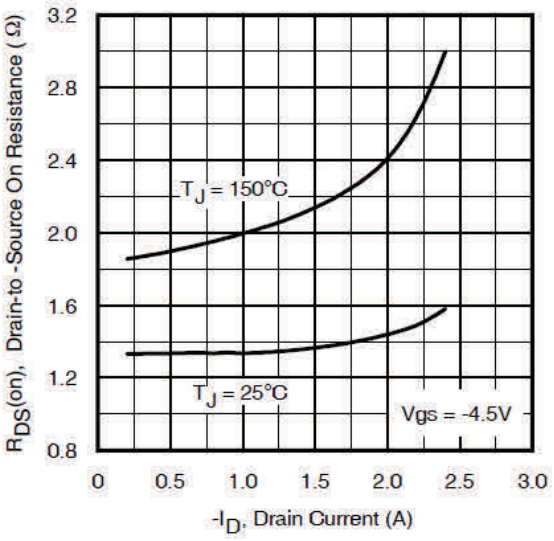


Fig 6. Typical On-Resistance Vs Drain Current

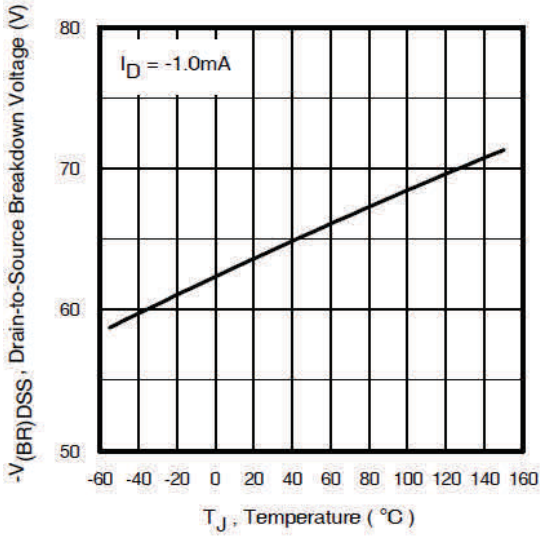


Fig 7. Typical Drain-to-Source Breakdown Voltage Vs Temperature

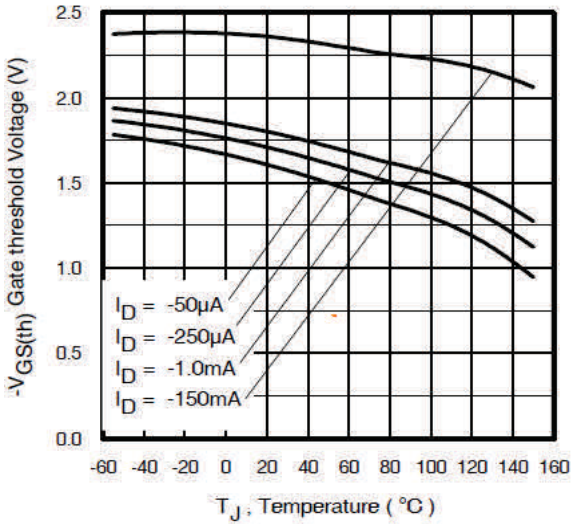


Fig 8. Typical Threshold Voltage Vs Temperature

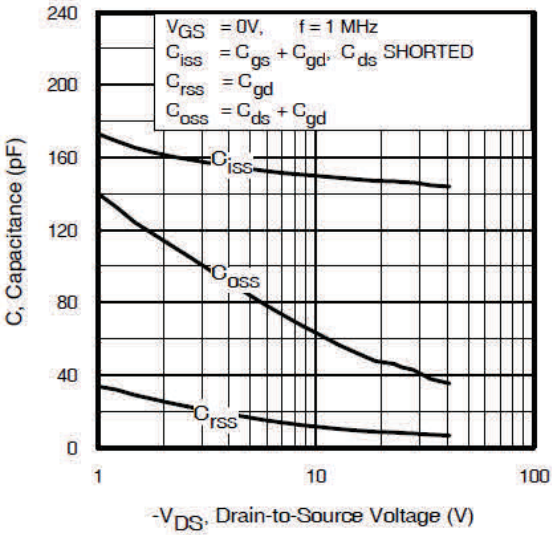


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

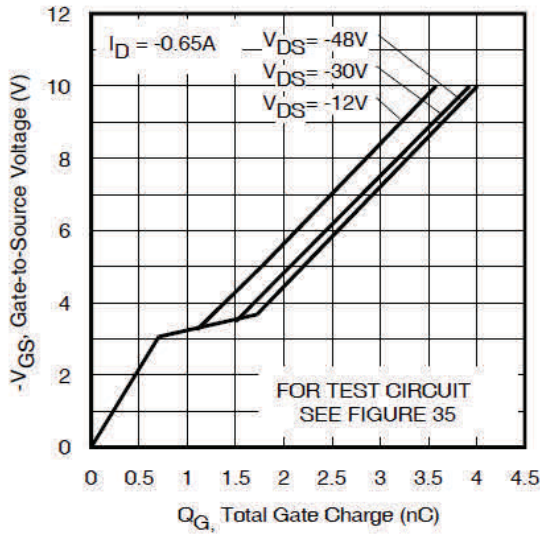


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

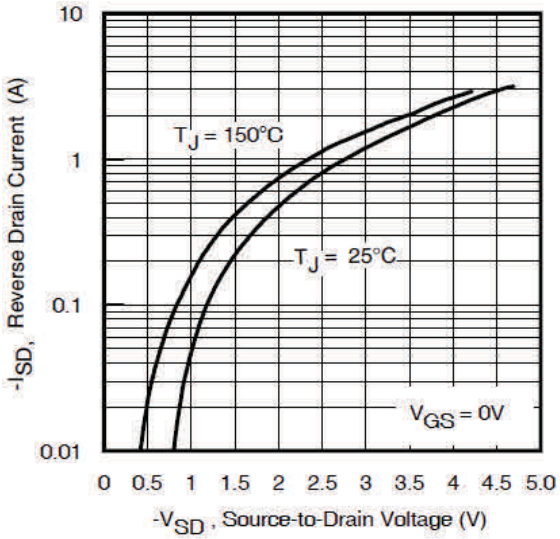


Fig 11. Typical Source-Drain Diode Forward Voltage

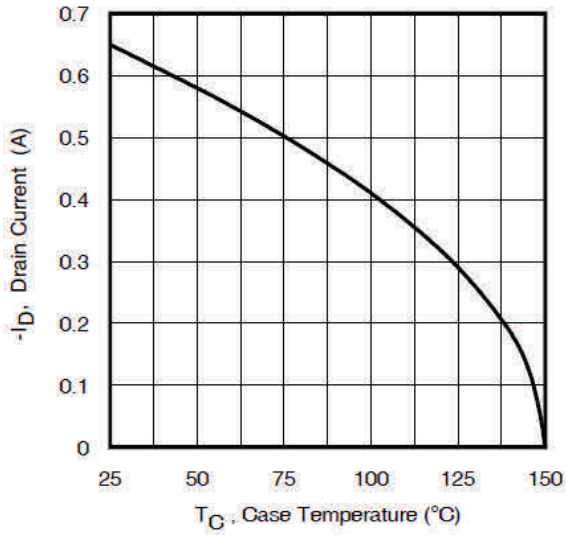


Fig 12. Maximum Drain Current Vs.Case Temperature

P-Channel
Die 2

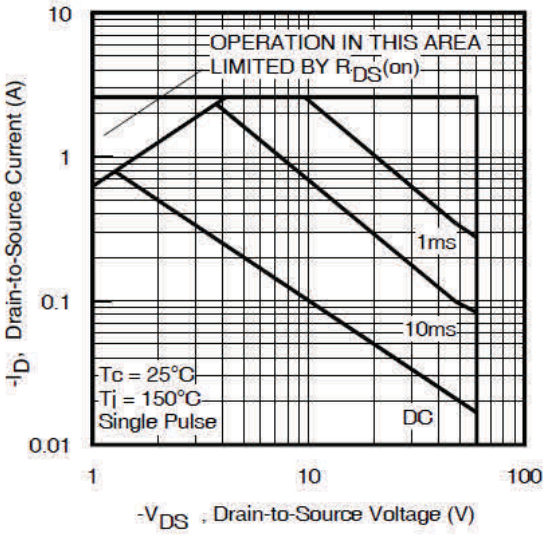


Fig 13. Maximum Safe Operating Area

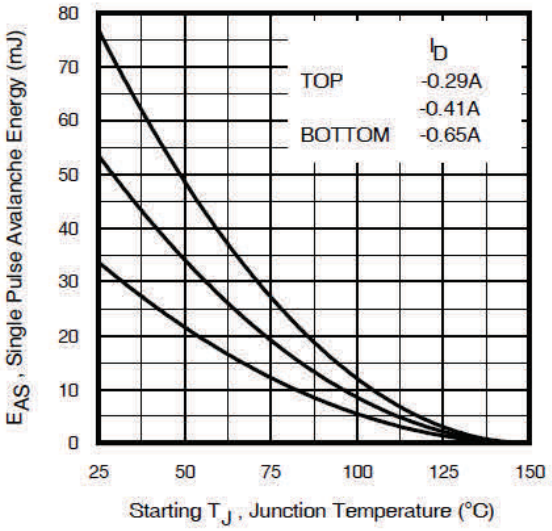


Fig 14. Maximum Avalanche Energy Vs. Drain Current

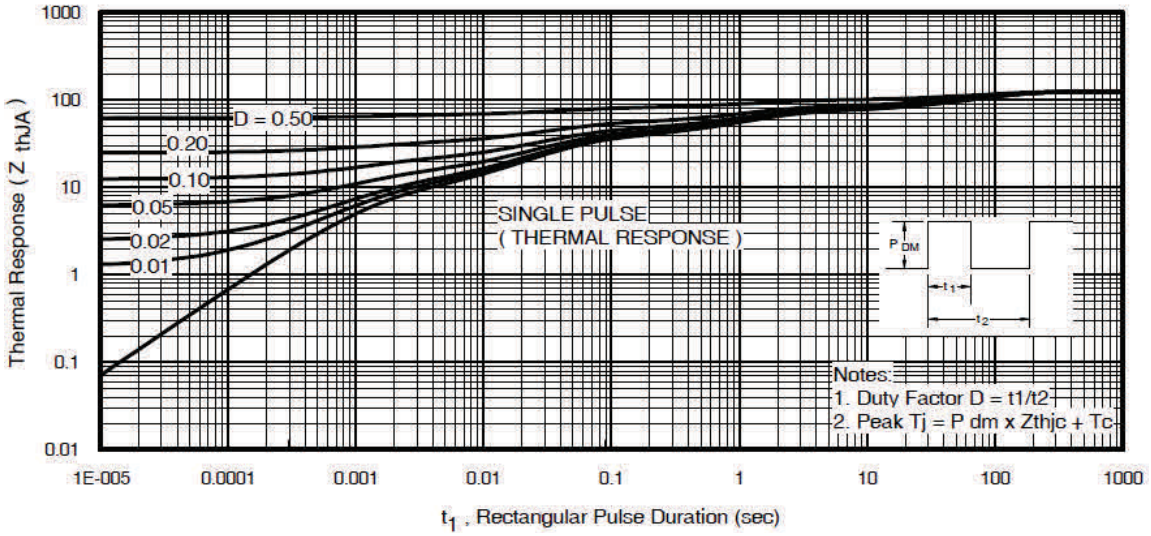


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

P-Channel
Die 2

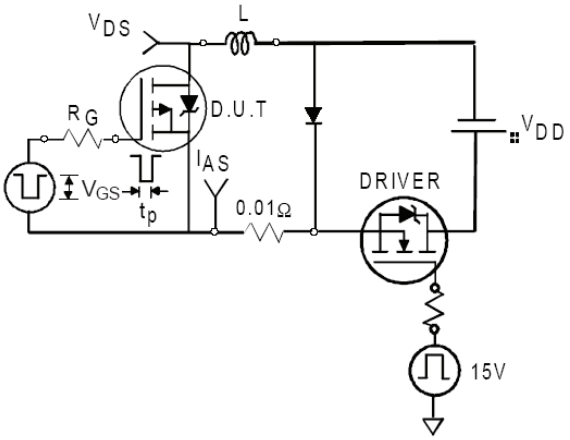


Fig 16a. Unclamped Inductive Test Circuit

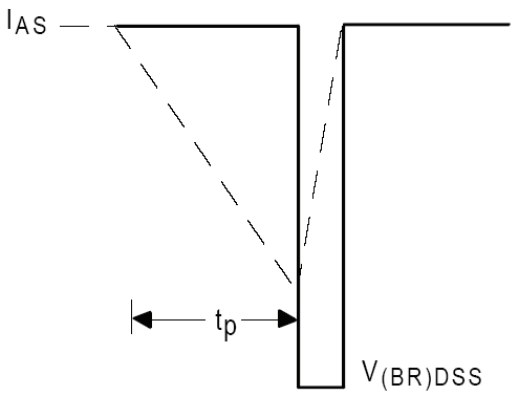


Fig 16b. Unclamped Inductive Waveforms

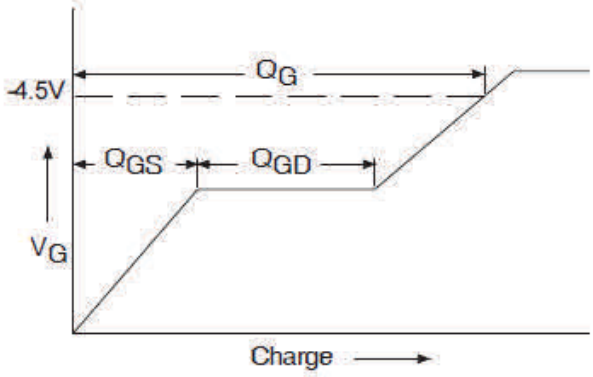


Fig 17a. Gate Charge Waveform

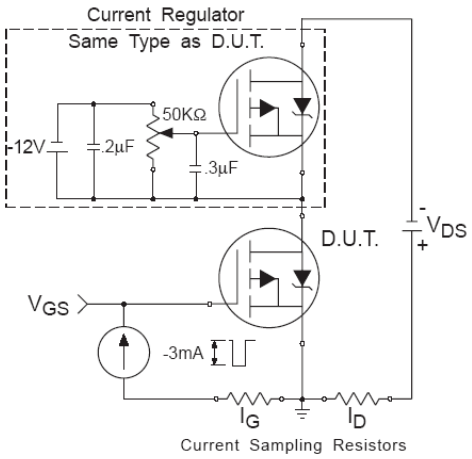


Fig 17b. Gate Charge Test Circuit

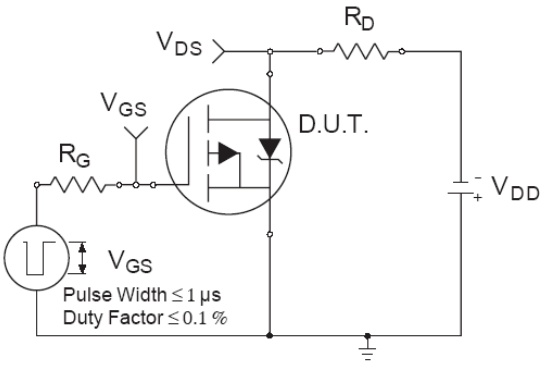


Fig 18a. Switching Time Test Circuit

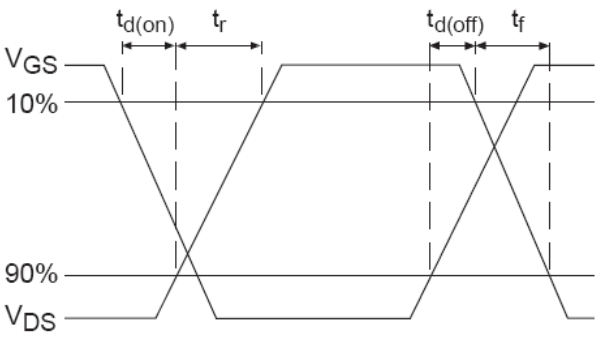
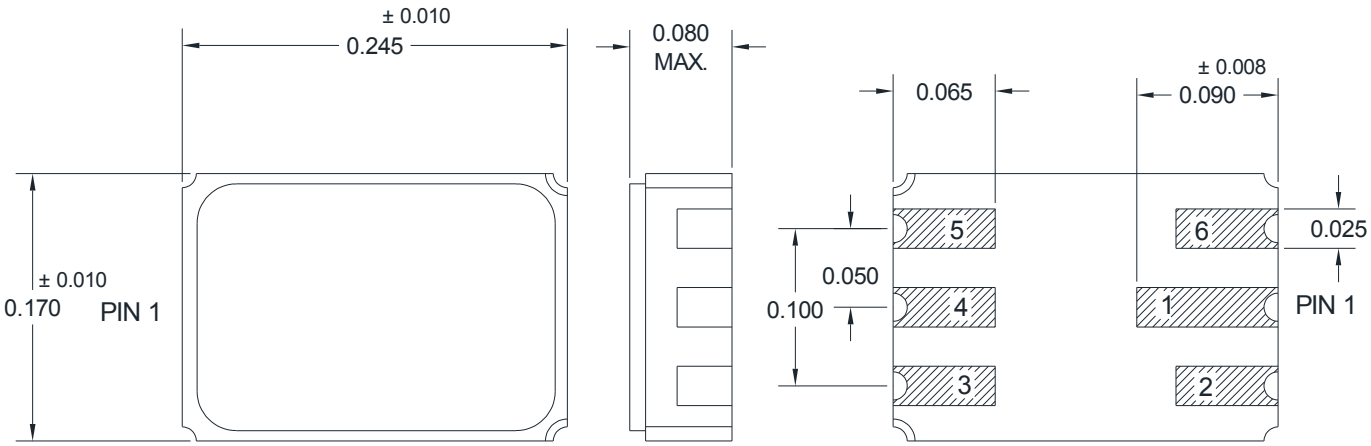


Fig 18b. Switching Time Waveforms

Case Outline and Dimensions - LCC-6



DIE 1 (N Ch)	PIN#
DRAIN	1
GATE	2
SOURCE	6

DIE 2 (P Ch)	PIN#
DRAIN	4
GATE	5
SOURCE	3

NOTES:

1. OUTLINE CONFORMS TO MIL-PRF-19500/255L
2. ALL DIMENSIONS ARE SHOWN IN INCHES.

An Infineon Technologies Company
www.infineon.com/irhirel

Infineon Technologies Service Center: USA Tel: +1 (866) 951-9519 and International Tel: +49 89 234 65555
Leominster, Massachusetts 01453, USA Tel: +1 (978) 534-5776
San Jose, California 95134, USA Tel: +1 (408) 434-5000
Data and specifications subject to change without notice.

IMPORTANT NOTICE

The information given in this document shall be in no event regarded as guarantee of conditions or characteristic. The data contained herein is a characterization of the component based on internal standards and is intended to demonstrate and provide guidance for typical part performance. It will require further evaluation, qualification and analysis to determine suitability in the application environment to confirm compliance to your system requirements.

With respect to any example hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind including without limitation warranties on non- infringement of intellectual property rights and any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's product and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of any customer's technical departments to evaluate the suitability of the product for the intended applications and the completeness of the product information given in this document with respect to applications.

For further information on the product, technology, delivery terms and conditions and prices, please contact your local sales representative or go to (www.infineon.com/hirel).

WARNING

Due to technical requirements products may contain dangerous substances. For information on the types in question, please contact your nearest Infineon Technologies office.

单击下面可查看定价，库存，交付和生命周期等信息

>>Infineon Technologies(英飞凌)